NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW60C** is Designed for 12.5 V High Band Applications up to 175 MHz.

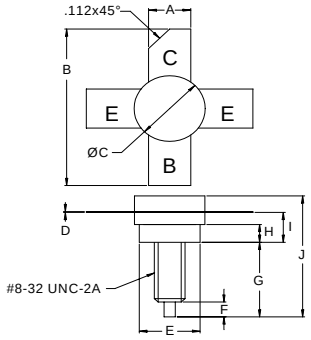
FEATURES:

- Common Emitter
- P_G = 5.0 dB at 45 W/175 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CESM}	36 V
V_{CEO}	16 V
V_{EBO}	4.0 V
P_{DISS}	100 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.75 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 50 mA	36			V
BV_{CEO}	I_C = 100 mA	16			
BV_{EBO}	I_E = 25 mA	4.0			V
I_{CES}	V_{CE} = 15 V			25	mA
h_{FE}	V_{CE} = 5.0 V I_C = 4.0 A	10		80	---
C_C	V_{CB} = 15 V f = 1.0 MHz			160	pF
G_P η_C	V_{CC} = 12.5 V P_{OUT} = 45 W f = 175 MHz	5.0 75			dB %

Specifications are subject to change without notice.